

2N5769
PN2369A

SILICON
NPN TRANSISTORS



TO-92 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5769 and PN2369A are epitaxial planar NPN Silicon Transistors designed for ultra high speed saturated switching applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

| | |
|--|--|
| Collector-Base Voltage | |
| Collector-Emitter Voltage | |
| Collector-Emitter Voltage | |
| Emitter-Base Voltage | |
| Continuous Collector Current | |
| Peak Collector Current | |
| Power Dissipation | |
| Operating and Storage Junction Temperature | |

| SYMBOL | | UNITS |
|----------------|-------------|------------------|
| V_{CBO} | 40 | V |
| V_{CES} | 40 | V |
| V_{CEO} | 15 | V |
| V_{EBO} | 4.5 | V |
| I_C | 200 | mA |
| I_{CM} | 500 | mA |
| P_D | 350 | mW |
| T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|---------------|---|-----|------|---------------|
| I_{CBO} | $V_{CB}=20\text{V}$ | | 400 | nA |
| I_{CBO} | $V_{CB}=20\text{V}, T_A=125^\circ\text{C}$ | | 30 | μA |
| I_{CES} | $V_{CE}=20\text{V}$ (2N5769) | | 400 | nA |
| I_{EBO} | $V_{EB}=4.5\text{V}$ (2N5769) | | 1.0 | μA |
| BV_{CBO} | $I_C=10\mu\text{A}$ | 40 | | V |
| BV_{CES} | $I_C=10\mu\text{A}$ | 40 | | V |
| BV_{CEO} | $I_C=10\text{mA}$ | 15 | | V |
| BV_{EBO} | $I_E=10\mu\text{A}$ | 4.5 | | V |
| $V_{CE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | | 200 | mV |
| $V_{CE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | | 250 | mV |
| $V_{CE(SAT)}$ | $I_C=100\text{mA}, I_B=10\text{mA}$ | | 500 | mV |
| $V_{BE(SAT)}$ | $I_C=10\text{mA}, I_B=1.0\text{mA}$ | 700 | 850 | mV |
| $V_{BE(SAT)}$ | $I_C=30\text{mA}, I_B=3.0\text{mA}$ | | 1.15 | V |
| $V_{BE(SAT)}$ | $I_C=100\text{mA}, I_B=10\text{mA}$ | | 1.6 | V |
| h_{FE} | $V_{CE}=0.35\text{V}, I_C=10\text{mA}$ (2N5769) | 40 | 120 | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=10\text{mA}$ (PN2369A) | 40 | 120 | |
| h_{FE} | $V_{CE}=0.4\text{V}, I_C=30\text{mA}$ | 30 | | |
| h_{FE} | $V_{CE}=1.0\text{V}, I_C=100\text{mA}$ | 20 | | |

R2 (7-November 2019)

2N5769
PN2369A

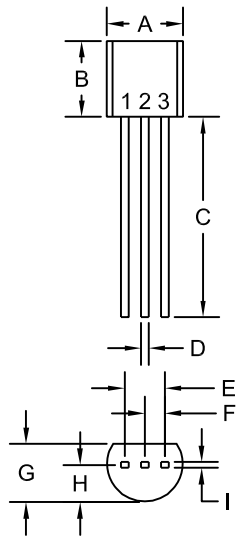
SILICON
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|-----------|--|-----|-----|-------|
| f_T | $V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$ | 500 | | MHz |
| C_{ob} | $V_{CB}=5.0\text{V}$, $I_E=0$, $f=140\text{kHz}$ | | 4.0 | pF |
| t_{on} | $V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$ | | 12 | ns |
| t_{off} | $V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=3.0\text{mA}$, $I_{B2}=1.5\text{mA}$ | | 18 | ns |
| t_s | $V_{CC}=10\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=10\text{mA}$ | | 13 | ns |

TO-92 CASE - MECHANICAL OUTLINE



R1

| SYMBOL | DIMENSIONS | | | |
|---------|------------|-------|-------------|------|
| | INCHES | | MILLIMETERS | |
| | MIN | MAX | MIN | MAX |
| A (DIA) | 0.175 | 0.205 | 4.45 | 5.21 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.500 | - | 12.70 | - |
| D | 0.016 | 0.022 | 0.41 | 0.56 |
| E | 0.100 | | 2.54 | |
| F | 0.050 | | 1.27 | |
| G | 0.125 | 0.165 | 3.18 | 4.19 |
| H | 0.080 | 0.105 | 2.03 | 2.67 |
| I | 0.015 | | 0.38 | |

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter
- 2) Base
- 3) Collector

MARKING: FULL PART NUMBER

R2 (7-November 2019)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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